

# RU4DSG

## GLASS PASSIVATED FAST RECOVERY RECTIFIER

VOLTAGE: 1500V

CURRENT: 3.0A

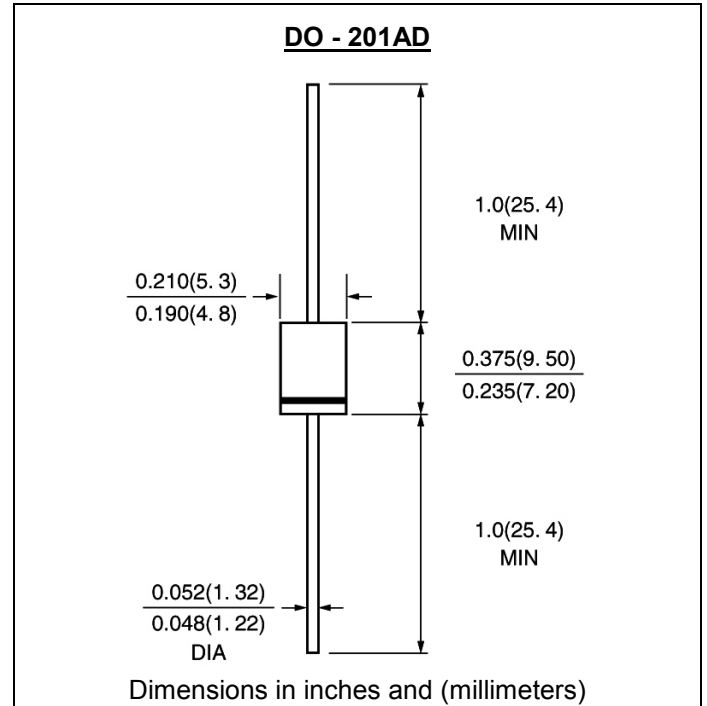


### FEATURE

Molded case feature for auto insertion  
High Switching Capability  
Low leakage current  
High surge capability  
High temperature soldering guaranteed  
250°C /10sec/0.375" lead length at 5 lbs tension  
Glass Passivated chip

### MECHANICAL DATA

Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C  
Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy  
Polarity: color band denotes cathode  
Mounting position: any



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half-wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

|   | SYMBOL                            | RU4DSG       | units |
|---|-----------------------------------|--------------|-------|
| Maximum Recurrent Peak Reverse Voltage  | V <sub>rrm</sub>                  | 1500         | V     |
| Maximum RMS Voltage   | V <sub>rms</sub>                  | 1050         | V     |
| Maximum DC blocking Voltage   | V <sub>dc</sub>                   | 1500         | V     |
| Maximum Average Forward Rectified Current 3/8" lead length at Ta =55°C            | I <sub>f(av)</sub>                | 3.0          | A     |
| Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load | I <sub>fsm</sub>                  | 125          | A     |
| Maximum Instantaneous Forward Voltage at rated forward current                    | V <sub>f</sub>                    | 1.6          | V     |
| Maximum full load reverse current full cycle at T <sub>L</sub> =75°C              | I <sub>r(av)</sub>                | 30           | μA    |
| Maximum DC Reverse Current at rated DC blocking voltage                           | I <sub>r</sub>                    | 5.0<br>500.0 | μA    |
| Typical Junction Capacitance (Note 1)   | C <sub>j</sub>                    | 50.0         | pF    |
| Maximum Reverse Recovery Time (Note 2)  | T <sub>rr</sub>                   | 120          | nS    |
| Storage and Operation Junction Temperature  | T <sub>stg</sub> , T <sub>j</sub> | -55 to +150  | °C    |

Note:

1. Measured at 1.0 MHz and applied voltage of 4.0Vdc
2. Test Condition I<sub>f</sub> =0.5A, I<sub>r</sub> =1.0A, I<sub>rr</sub> =0.25A

## RATINGS AND CHARACTERISTIC CURVES RU4DSG

